

HD34386

MEMS Band Pass Filter

Features:

- Pass Band : 1.5 ~ 1.95 GHz
- Insertion Loss : 2.7dB
- Size : 7.5x20.0x0.5mm

Absolute Maximum Ratings

- Max. Input Power : +35dBm
- Storage Temperature : -55 ~ +85Deg.C
- Operating Temperature : -55 ~ +125Deg.C



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

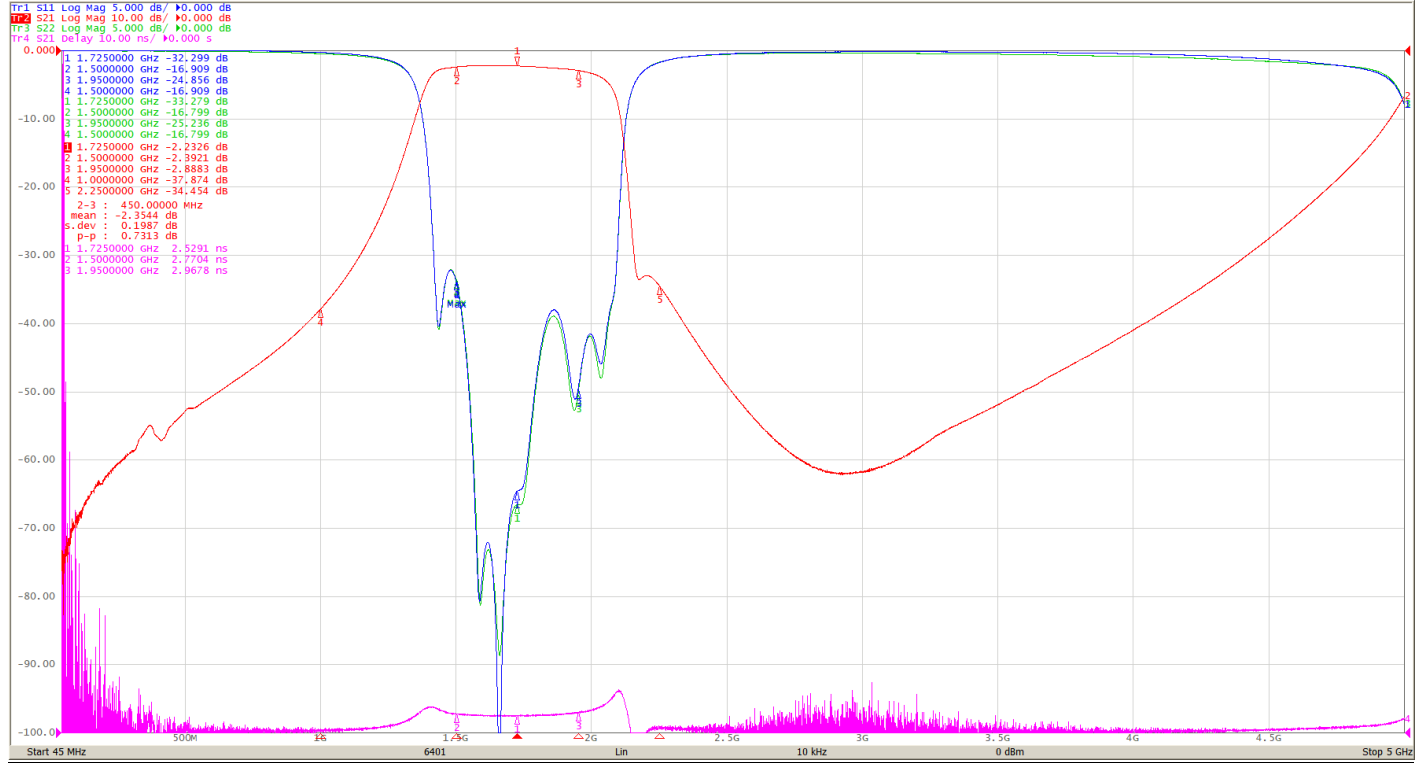
Electrical Specifications (TA=+25Deg.C, 50Ω system)

Parameter	Min.Value	Typical Value	Max.Value	Unit	
Frequency Range	1.5 ~ 1.95			GHz	
Insertion Loss (Fc)	-	2.23	2.7	dB	
Ripple	-	0.73	1.0	dB	
Attenuation	DC~@1GHz	30	37.87	-	dB
	@2.25GHz	30	34.45	-	dB
Return Loss	15.0	16.79	-	dB	
Group Delay	-	2.96	4.5	ns	

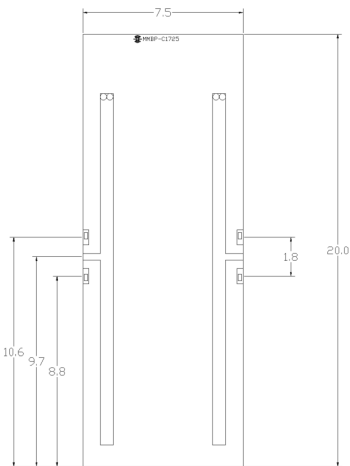
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Test Curve



Size

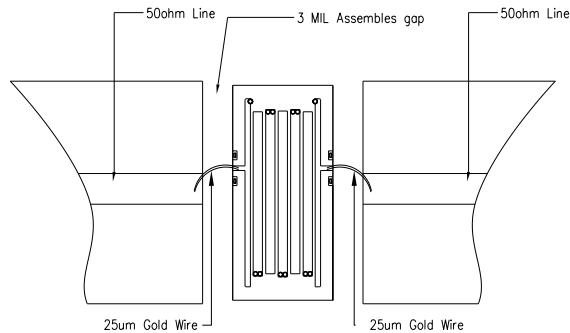


- Remarks: Unit : mm, Tolerance : ± 0.25 mm
1. Chip bottom is gold plated and grounded.
 2. Bonding pressure points are gold plated.
 3. Don't bond on the through holes.

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Applications

1. Assembly and Bonding Diagram. (Reference)



Assembly Diagram

2. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
3. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/°C) with Silicon, thickness 0.2mm max.
4. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
5. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.